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# BT136S-XXXE(MS)

Product specification





#### **DESCRIPTION**

The BT136S-XXE(MS) series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.

#### **MAIN FEATURES**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	4	А
VDRM /VRRM	600/800	V

#### **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking	
MSKS 2 SERICONOLLIOR	T2(2) T1(1)	MSKSEMI BT136S-600E MS XXX	MSKSEMI BT136S-800E MS XXX
3		BT136S-600E(MS)	BT136S-800E(MS)

Notes:XXX represents the order code.

#### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit	
Storage junction temperature range		Tstg	-40-150	$^{\circ}\mathbb{C}$
Operating junction temperature rang	је	Tj	-40-125	$^{\circ}$ C
Repetitive peak off-state voltage(T <sub>j</sub> =	<b>25</b> ℃)	VDRM	600/800	V
Repetitive peak reverse voltage(T <sub>j</sub> =2	25℃)	VRRM	600/800	V
RMS on-state current(TC=100℃)		I <sub>T(RMS)</sub>	4	Α
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	35	А
Pt value for fusing (tp=10ms)		I²t	6.1	A <sup>2</sup> s
Critical rate of rise of on-state I - II - III			50	A/µs
current (I <sub>G</sub> =2×I <sub>GT</sub> )		dl/dt	10	
Peak gate current		Ідм	2	А
Average gate power dissipation		P <sub>G(AV)</sub>	0.5	W
Peak gate power		P <sub>GM</sub>	5	W



# **ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
la-		I - II -III	MAX	10	^
lgт	V <sub>D</sub> =12V	IV	IVIAA	25	mA
V <sub>GT</sub>		ALL	MAX	1.3	V
V <sub>GD</sub>	$V_D=V_{DRM} T_j=125 ^{\circ}C$ RL=3.3K $\Omega$	ALL	MIN	0.2	V
	L I <sub>G</sub> =1.2I <sub>GT</sub>	I -III	MAX	30	m A
IL.		IG=1.2IGT	IVIAA	45	mA
Ін	h=100mA		MAX	25	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125℃		MIN	100	V/µs
(dV/dt)c	(dl/dt)c=1.7A/ms T <sub>j</sub> =125℃		MIN	0.5	V/µs

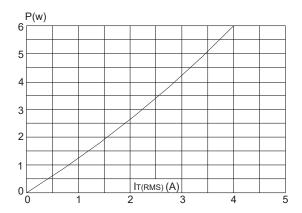
# STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
Vтм	Ітм=5.5Atp=380µs	Tj=25℃	1.6	V
IDRM	VD=VDRM VR=VRRM	Tj=25℃	5	μA
IRRM		Tj=125℃	0.5	mA

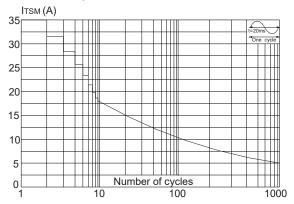
#### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-c)	junction to case(AC)	2.8	°C/W
Rth(j-a)	junction to ambient	70	°C/W

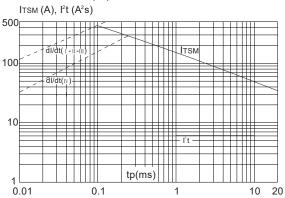
FIG.1: Maximum power dissipation versus RMS on-state current



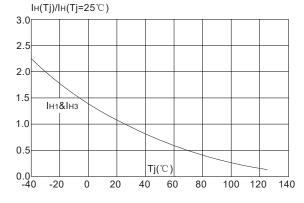
**FIG.3:** Surge peak on-state current versus number of cycles



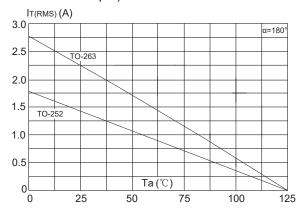
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of  $I^2t$  ( I - II - III : dI/dt < 50A/ $\mu$ s; IV:dI/dt < 10A/ $\mu$ s)



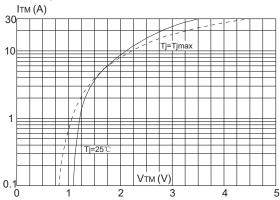
**FIG.7:** Relative variations of holding current versus junction temperature



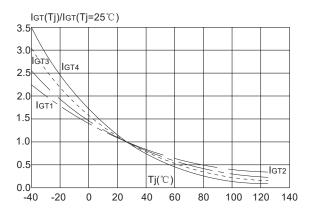
**FIG.2:** RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm)



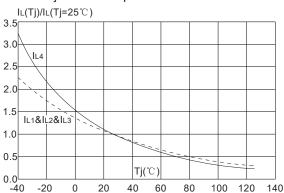
**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current versus junction temperature

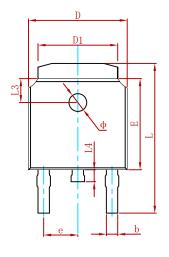


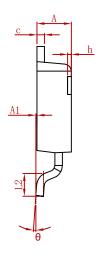
**FIG.8:** Relative variations of latching current versus junction temperature

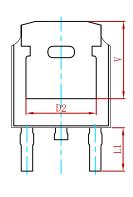




#### **PACKAGE MECHANICAL DATA**

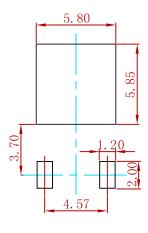






nbol Dimensions In Millimeters		Dimension	s In Inches
Min.	Max.	Min.	Max.
2.200	2.400	0.087	0.094
0.000	0.127	0.000	0.005
0.635	0.770	0.025	0.030
0.460	0.580	0.018	0.023
6.500	6.700	0.256	0.264
5.100	5.460	0.201	0.215
4.830	REF.	0.190	REF.
6.000	6.200	0.236	0.244
2.186	2.386	0.086	0.094
9.712	10.312	0.382	0.406
2.900	REF.	0.114	REF.
1.400	1.700	0.055	0.067
1.600 REF.		0.063	REF.
0.600	1.000	0.024	0.039
1.100	1.300	0.043	0.051
0°	8°	0°	8°
0.000	0.300	0.000	0.012
	Min. 2.200 0.000 0.635 0.460 6.500 5.100 4.836 6.000 2.186 9.712 2.900 1.400 0.600 1.100 0°	Min.         Max.           2.200         2.400           0.000         0.127           0.635         0.770           0.460         0.580           6.500         6.700           5.100         5.460           4.830 REF.         6.000           2.186         2.386           9.712         10.312           2.900 REF.         1.400           1.600 REF.         0.600           1.100         1.300           0°         8°	Min.         Max.         Min.           2.200         2.400         0.087           0.000         0.127         0.000           0.635         0.770         0.025           0.460         0.580         0.018           6.500         6.700         0.256           5.100         5.460         0.201           4.830 REF.         0.190           6.000         6.200         0.236           2.186         2.386         0.086           9.712         10.312         0.382           2.900 REF.         0.114           1.400         1.700         0.055           1.600 REF.         0.063           0.600         1.000         0.024           1.100         1.300         0.043           0°         8°         0°

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
BT136S-XXE(MS)	TO-252	2500



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